

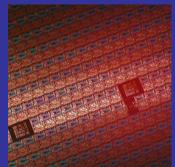
#### Accelerating the next technology revolution

# Sept 2013 Resist TWG Survey Results



Karen Petrillo – SEMATECH/IBM Serge Tedesco – CEA-LETI Kyoungyong Cho – SEMATECH/Samsung

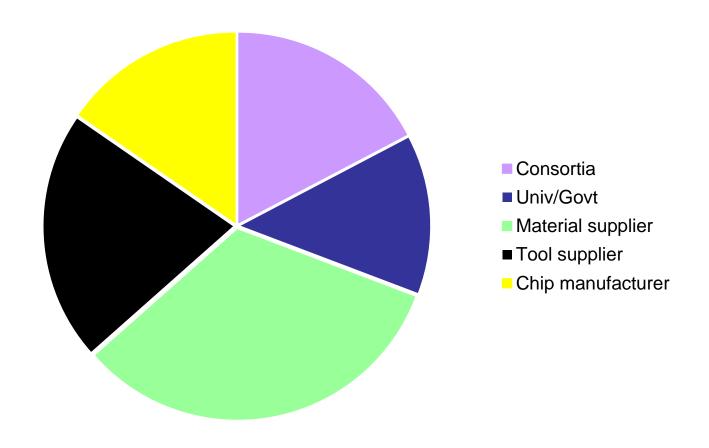




## **IEUVI** Resist TWG Attendance



52 people attended



# Meeting Focus



- Outgas testing
  - Major issue limiting materials research and development. Focusing on this issue for the past several meetings
    - Testing availability is improving
    - Ability to research topics related to outgassing is becoming available
- Interest in DSA as a means to compliment traditional lithography

## Agenda



NIST Outgas Testing Update	S.	Hill,	NIST
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ROX Outgas Testing Update G. Denbeaux, C
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Break

EUVT Outgas Testing Update R. Perera, EUV Technology

DSA as a Mean for EUV Contact Rectification R. Gronheid, IMEC

DSA as Complementary Lithography: R. Tiron, CEA-Leti
Guiding Pattern Requirements for Contact

Shrink and Contact Multiplication

Summary S. Tedesco, CEA-Leti

# NIST update, Shannon Hill



- 21 customer samples tested to date, 100 % passing
- Focusing on metrology

Some facilities are having problems exposing high E0 materials in the 1 hour window.

Expose for longer time

Expose a smaller area in an hour

Need to make sure you are working in the contamination limited zone

High partial pressures during outgassing can result in non-mass-limited CG and hence *underestimates* for outgas-testing CG for either EUV or ebeam exposures.

•Mass-limited growth should be verified for high-outgassing resists (e.g., check that CG thickness profile does NOT follow intensity profile of beam.)

## EIDEC update, Eishi Shiobara



- 60 customer samples tested, 80% passing
- Studied the effect of formulation and process parameters on contamination growth, and recommended ways to reduce testing
  - Considering protecting unit ratio and PAG loading; clear correlation with contamination thickness was obtained for both parameters. However, this correlation was not the same for dose.
  - Considering quencher loading and PEB temperature; clear correlation with contamination thickness was obtained for both parameters. For these parameters, a clear correlation with dose was also observed.
  - Guidelines on resist outgas test sample reduction were suggested. (based on evaluated data)

# ROX Update, Greg Denbeaux



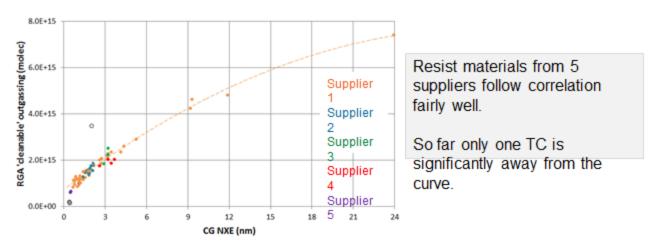
- 81 customer samples tested, 55% passing
- Residual contamination from stray electrons discussed
- Residual contamination in the chamber
  - 2 hour delay between samples is the current methodology to deal with chamber outgassing
- High E0 samples
  - No correlation between high E0 samples and CG

## IMEC update, Ivan Pollentier



- 69 customer samples tested, 70% passing
- Good correlation of RGA to CG on witness sample
  - Suggestion from audience to use RGA as a screening method, and only do WS testing for samples that are on the pass/fail borderline

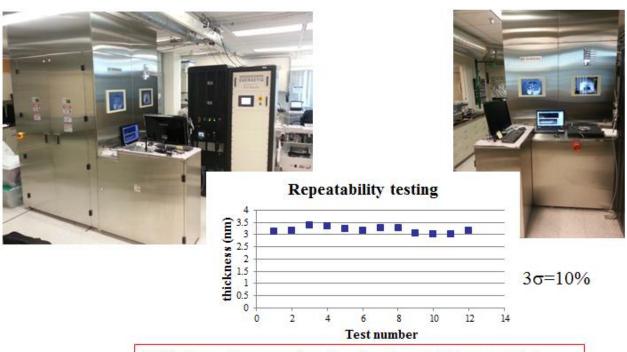
## Check of correlation in 72 resist tests so far



## EUVT update, Rupert Perera



- 3 customer samples tested, tool is currently undergoing maintenance
- Showed good repeatability testing
- Residual contamination from stray electrons is an issue
  - Oxygen plasma cleaning is not the answer



High throughput tool – plan for over 1000 materials/year

## DSA for EUV contact rectification, Roel Gronheid



- Grapho-epitaxy based on homo-polymer blends works, but only to maintain the relative CDU performance in combination with shrink
- Grapho-epitaxy based on BCP requires very large initial hole CD and may not be attractive path for dense hole patterns
- Chemo-epitaxy DSA flow with BCP looks promising, but does not yet meet requirements
  - Repair is not perfect
  - Some pitches and geometries don't work well

#### GRAPHO-EPITAXY WITH BCP

193nm pre-pattern

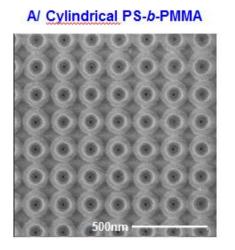
	Pst-Litho	Pst-HardBake	Pst-DSA + Wet Dev
SEM image			
CD (nm)	53.8	58.9	14.5
Change (nm, %)	275	+5.1, +9.5%	-44.4, -75.4%
Net Shrink (nm, %)	-	-	-39.3, -73.0%
CD Range (nm)	3.4	3.3	0.5

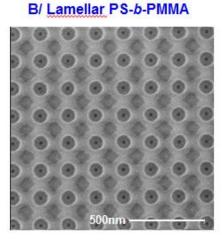
## DSA for contact shrink and multiplication, R. Tiron



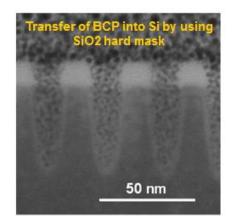
- DSA is a complementary lithography technique that could be inserted as early as the 14nm node
  - In a first step by using PS-b-PMMA like materials (lowest CD after etching 10nm)
  - In a second step by using high  $\chi$  materials (CD < 10nm)

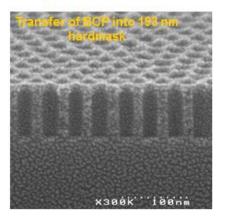
#### Contact shrink vs. BCP morphology





# BCP Etching: capabilities demonstration on small samples





## Feb 2013 Outgas tool status & capacity





				SEMAI ECIT
I	Status	Tested as of Oct 2012	Tested to date	Current Throughput (samples per month)
ROX	Up and running	53	81	8 → 24
EUVT	August delivery, working towards Q4 certification & customer availability	0	3	40 - 80
NIST	Certified Aug/Sept 2011	9	21	6
EIDEC (LTJ)	Certification complete, ready to start	0	60	30 - 40
IMEC	Recently certified	10	69	~20
LTJ – 3 private	Certified		no data	no data
Total number of				
Customer samples				
tested		62	234	~70
Projected Total Capacity				145

Industry request: 250 per month, same as MET tools

## Tool status



	Total	Total passing	% passing
NIST	21	21	100%
EIDEC	60	48	80%
ROX	80	45	55%
IMEC	69	48	70%
EUVT	3	3	

## Summary



- Comparison between outgas tools: Some samples passing at one site but failing at another
  - Request failing sample testing at multiple sites
  - Follow up by e-mail with material suppliers and consortium testing facilities
- Non-cleanables
  - 100% passing
  - Is this useful?
- RGA comparison
  - Is there a way to implement
  - Suggestion: screen with RGA, and only witness test samples that are on the borderline